

On p. 21, the Abstract has been replaced with the paragraph shown below:

**ABSTRACT OF THE DISCLOSURE**

B2  
Memory integrated circuitry includes an array of memory cells formed over a semiconductive substrate and occupying area thereover, at least some memory cells of the array being formed in lines of active area formed within the semiconductive substrate which are continuous between adjacent memory cells. Adjacent memory cells are isolated from one another relative to the continuous active area formed therebetween by a conductive line formed over said continuous active area between said adjacent memory cells. At least some adjacent lines of continuous active area within the array are isolated from one another by LOCOS field oxide formed therebetween. The respective area consumed by individual memory cells is less than  $8F^2$ , where "F" is no greater than 0.25 micron.